WHAT IS CLAIMED IS:

1. A magnetoresistive head comprising:

a lower magnetic shield formed on a substrate;

a magnetic domain control underlayer formed on the lower magnetic shield;

a multi-layered film having an underlayer formed on the magnetic domain control underlayer, a free layer, a non-magnetic layer, a pinned layer, and an anti-ferromagnetic layer for pinning the magnetizing direction of the pinned layer;

a magnetic domain control film formed on the magnetic domain control underlayer, said magnetic domain control film being in contact with both of lateral ends in the direction of the track width of the free layer, for conducting magnetic domain control of the free layer;

a pair of electrode films for supplying an electric current to the multi-layered film; and

an upper magnetic shield formed on the multi-layered film and the electrode film.

2. A magnetoresistive head comprising:

a lower magnetic shield formed on a substrate;

a magnetic domain control underlayer formed on the lower magnetic shield;

a multi-layered film having an underlayer formed on the magnetic domain control underlayer, a free layer, a non-magnetic layer, a pinned layer, and an anti-ferromagnetic layer for pinning the magnetizing direction of the pinned layer;

a magnetic domain control film formed on the magnetic domain control underlayer, said magnetic domain control film being in contact with both of lateral ends in the direction of the track width of the free layer, for conducting magnetic domain control of the free layer;

a dielectric film formed on the magnetic domain control film; and

an upper magnetic shield formed on the multi-layered film and the dielectric film.

3. The magnetoresistive head of claim 1 wherein the magnetic domain control underlayer is formed of a non-magnetic material selected from one or more of Cr, Ti, w, Mo, V, Mn, Nb, and Ta.

4. The magnetoresistive head of claim 1 wherein a relation between a film thickness of the magnetic domain control underlayer defined as tUL, and a distance between the upper end of the magnetic domain control underlayer and the lowermost portion of the magnetic domain control film defined as OM is: $0 \leqq OM \leqq tUL$.

5. The magnetoresistive head of claim 1 or 2 or 3 or 4 wherein the relation between tUL and OM is: $0.8 \leqq OM \leqq tUL\ 2.2$.

6. A method of manufacturing a magnetoresistive head comprising:

depositing a lower magnetic shield on a substrate;

depositing a magnetic domain control underlayer on the lower magnetic shield;

forming, on the magnetic domain control underlayer, a multi-layered film comprising an underlayer, a free layer, a non-magnetic layer, a pinned layer, and an anti-ferromagnetic layer for pinning the magnetizing direction of the pinned layer in one direction;

forming a resist layer on a portion of the multi-layered film;

removing portions of the multi-layered film and the magnetic domain control underlayer not covered with the resist layer;

depositing a magnetic domain control film on the lateral side in the direction of the track width of the multi-layered film and on the magnetic domain control underlayer on both sides thereof;

depositing an electrode film on the magnetic domain control film;

removing the resist layer; and

forming an upper magnetic shield on the electrode film and the multi-layered film.

7. The method of manufacturing a magnetoresistive film of claim 6, and further comprising heating the substrate.

8. A method of manufacturing a magnetoresistive head comprising:

depositing a lower magnetic shield on a substrate;

depositing a magnetic domain control underlayer on the lower magnetic shield;

forming, on the magnetic domain control underlayer, a multi-layered film comprising an underlayer, a free layer, a non-magnetic layer, a pinned layer, and an anti-ferromagnetic layer for pinning the magnetizing direction of the pinned layer in one direction;

forming a resist layer on a portion of the multi-layered film;

removing portions of the multi-layered film and the magnetic domain control underlayer not covered with the resist layer;

depositing a magnetic domain control film on the lateral side in the direction of the track width of the multi-layered film and on the magnetic domain control underlayer on both sides thereof;

depositing a dielectric film on the magnetic domain control film;

removing the resist layer; and

forming an upper magnetic film shield on the electrode film and the dielectric film.

9. The method of manufacturing a magnetoresistive film of claim 6 or 7 or 8 wherein said removing includes milling.

10. The method of manufacturing a magnetoresistive film of claim 9 wherein said milling is ion milling.